

**isc Silicon NPN Power Transistor**

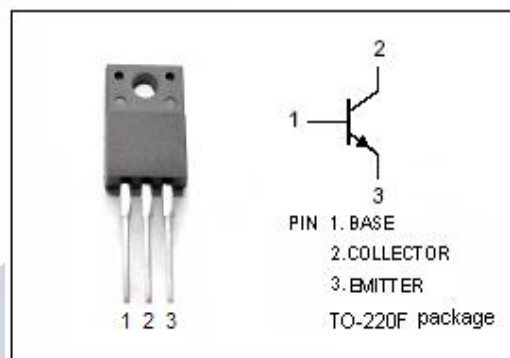
**2SC4793**

**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 230V(\text{Min})$
- High Current-Gain Bandwidth Product
- Complement to Type 2SA1837
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

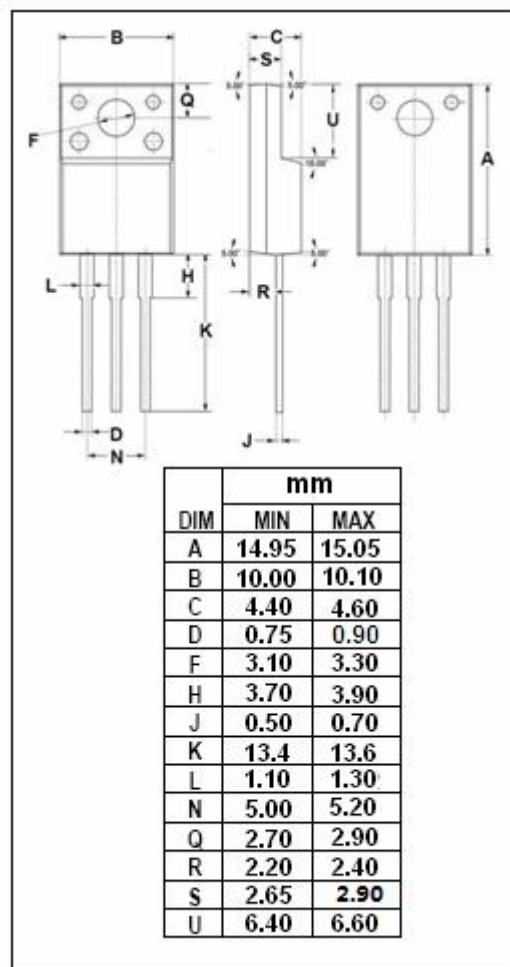
**APPLICATIONS**

- Power amplifier applications.
- Driver stage amplifier applications



**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	230	V
$V_{CEO}$	Collector-Emitter Voltage	230	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	1	A
$I_B$	Base Current-Continuous	0.1	A
$P_C$	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	20	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor****2SC4793****ELECTRICAL CHARACTERISTICS****T<sub>j</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	230			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 500mA; I <sub>B</sub> = 50mA			1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 500mA ; V <sub>CE</sub> = 5V			1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 230V ; I <sub>E</sub> =0			1.0	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> =0			1.0	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 100mA; V <sub>CE</sub> = 5V	100		320	
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1MHz		20		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 100mA ; V <sub>CE</sub> = 10V		100		MHz